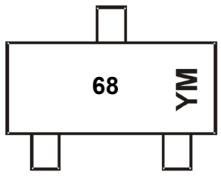
Marking Information

SOT23



68 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: B = 2014)
M or $\overline{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2014	……	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	B	……	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±12	V
Drain Current (Note 6) V_{GS}= -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-3.3 -2.6	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-3.9 -3.2	A
Pulsed Drain Current (Pulse width ≤10μS, Duty Cycle ≤1%)			I_{DM}	-18	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	182	°C/W
	t<10s		133	
Total Power Dissipation (Note 6)		P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	103	°C/W
	t<10s		75	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1in. square copper plate.

Electrical Characteristics (@ T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	—	-1.3	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	57 64 80 107	72 85 120 165	mΩ	V_{GS} = -10V, I_D = -4.2A V_{GS} = -4.5V, I_D = -4.0A V_{GS} = -2.5V, I_D = -2.0A V_{GS} = -1.8V, I_D = -1.0A
Diode Forward Voltage	V_{SD}	—	—	-1.2	V	V_{GS} = 0V, I_S = -1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	708	—	pF	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	57	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	47	—	pF	
Gate Resistance	R_G	—	14	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_G	—	7.3	—	nC	V_{DS} = -15V, I_D = -4A
Total Gate Charge (V_{GS} = -10V)	Q_G	—	15.9	—	nC	V_{DS} = -15V, I_D = -4A
Gate-Source Charge	Q_{GS}	—	1.2	—		
Gate-Drain Charge	Q_{GD}	—	1.7	—		
Turn-On Delay Time	$t_{d(on)}$	—	3.5	—	ns	V_{DS} = -15V, V_{GS} = -10V, I_D = -4A, R_G = 6.0Ω
Rise Time	t_r	—	15.8	—		
Turn-Off Delay Time	$t_{d(off)}$	—	70.3	—		
Fall Time	t_f	—	33.9	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

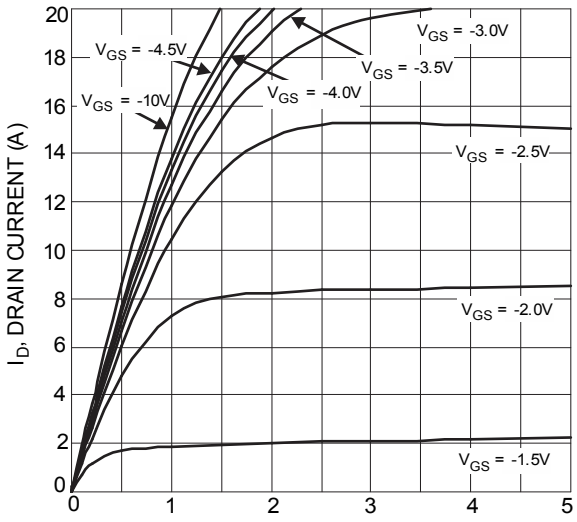


Figure 1 Typical Output Characteristics

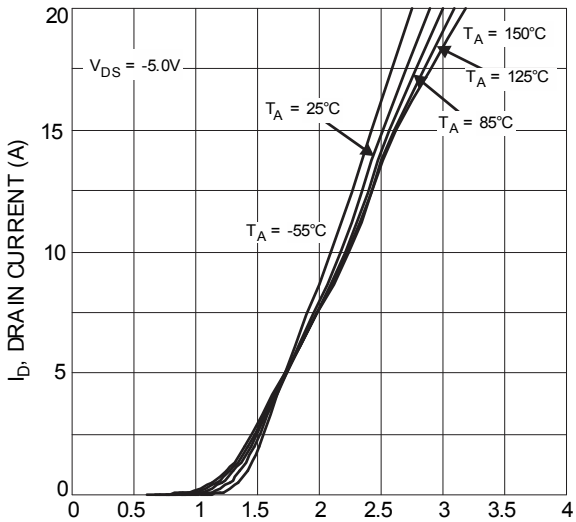


Figure 2 Typical Transfer Characteristics

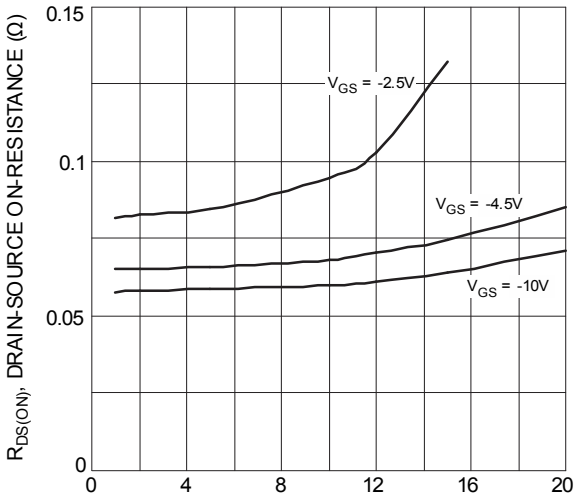


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

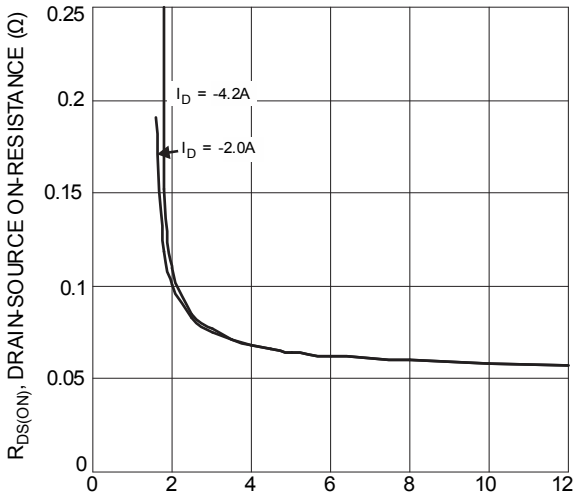


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

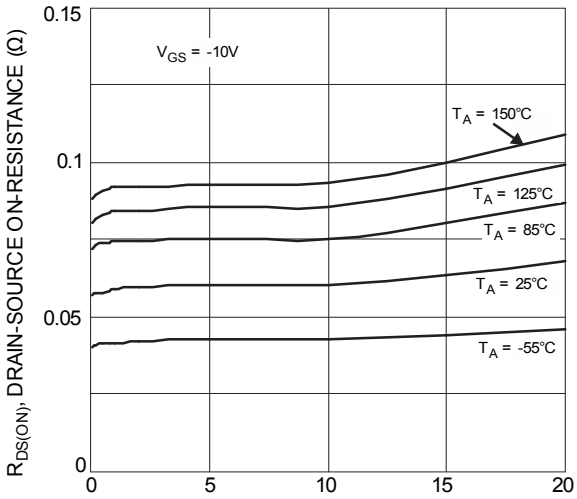


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

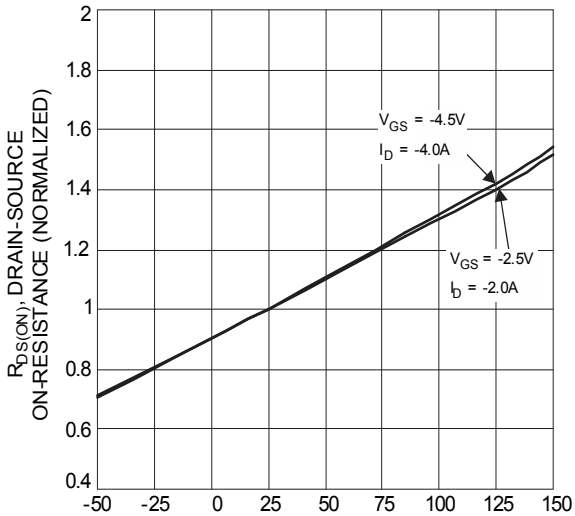


Figure 6 On-Resistance Variation with Temperature

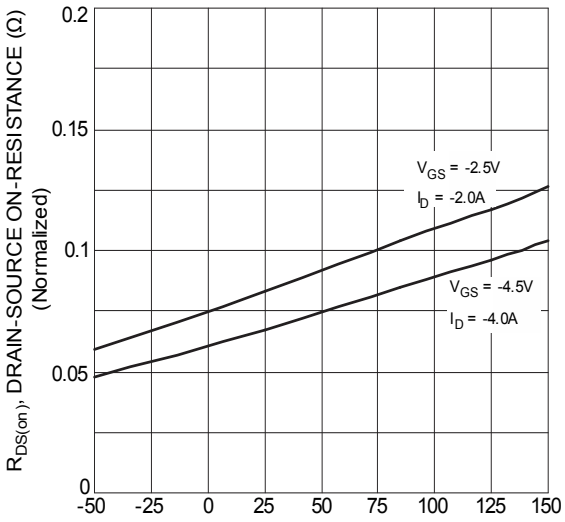


Figure 7 On-Resistance Variation with Temperature

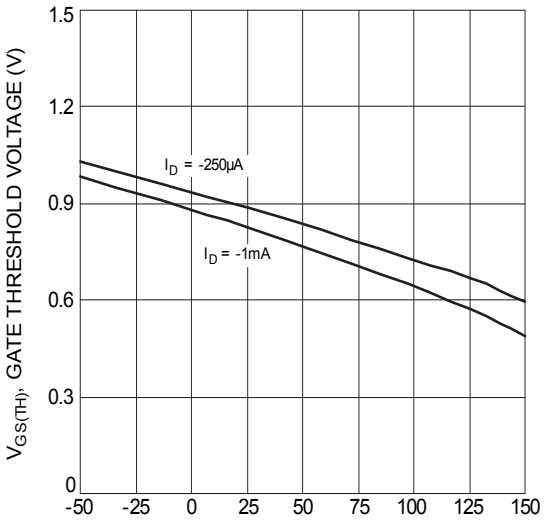


Figure 8 Gate Threshold Variation vs. Ambient Temperature

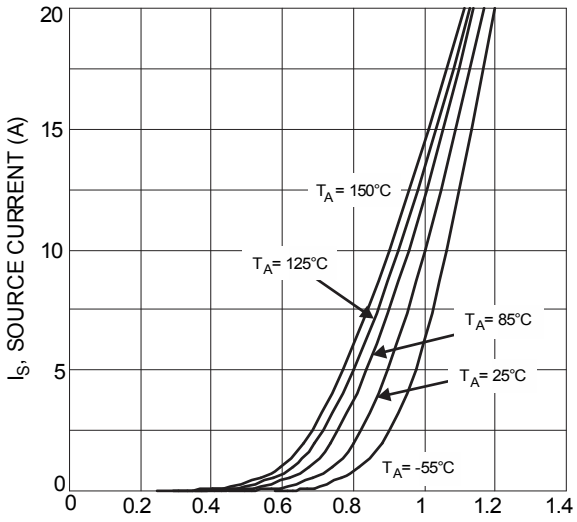


Figure 9 Diode Forward Voltage vs. Current

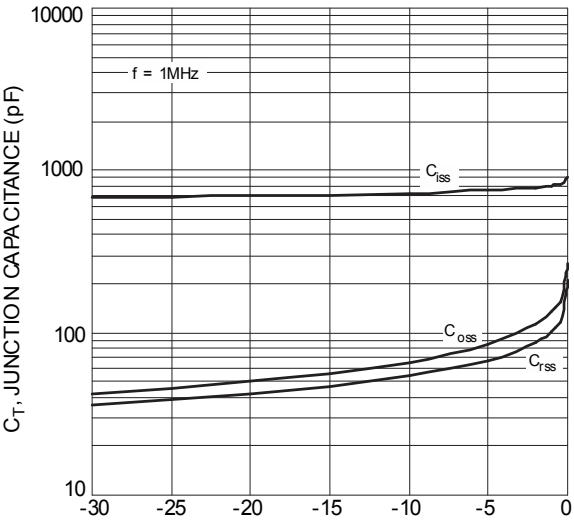


Figure 10 Typical Junction Capacitance

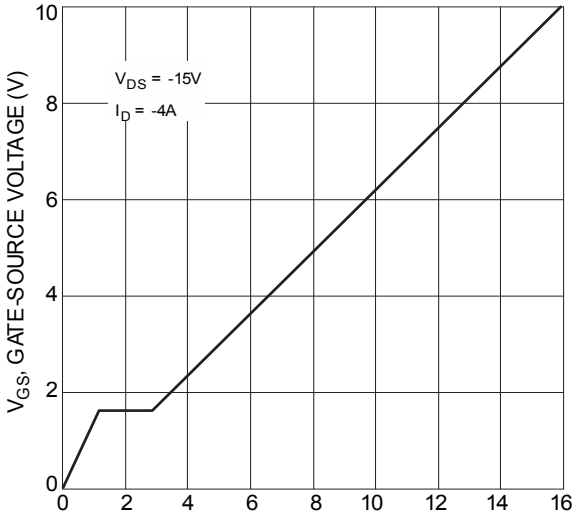


Figure 11 Gate-Charge Characteristics

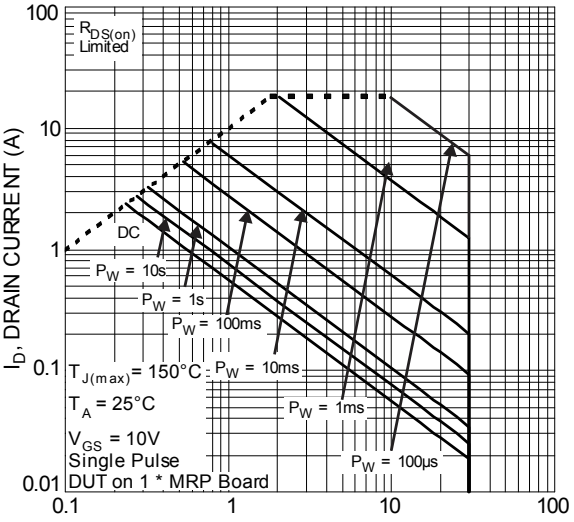


Figure 12 SOA, Safe Operation Area

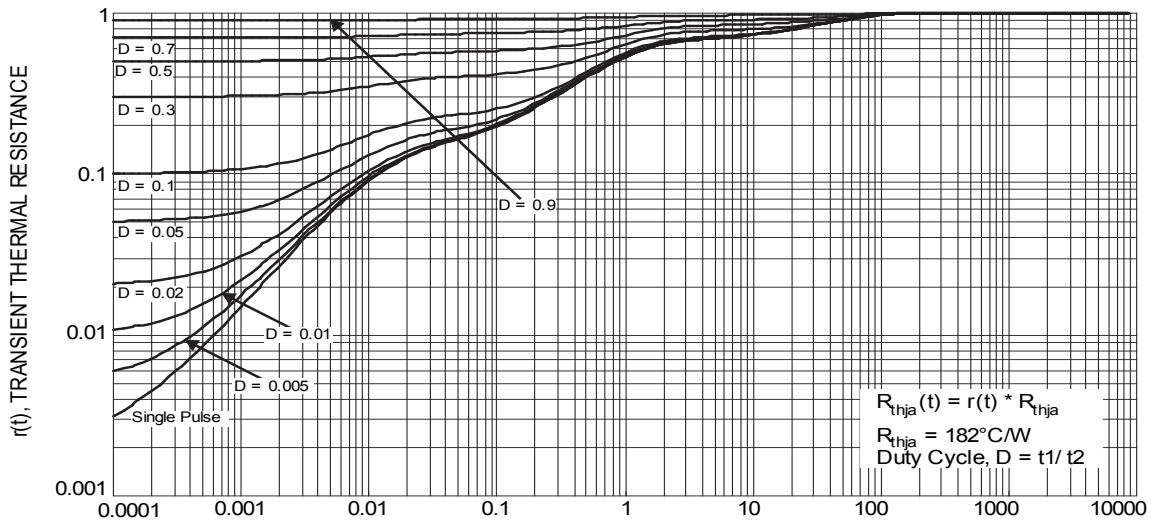
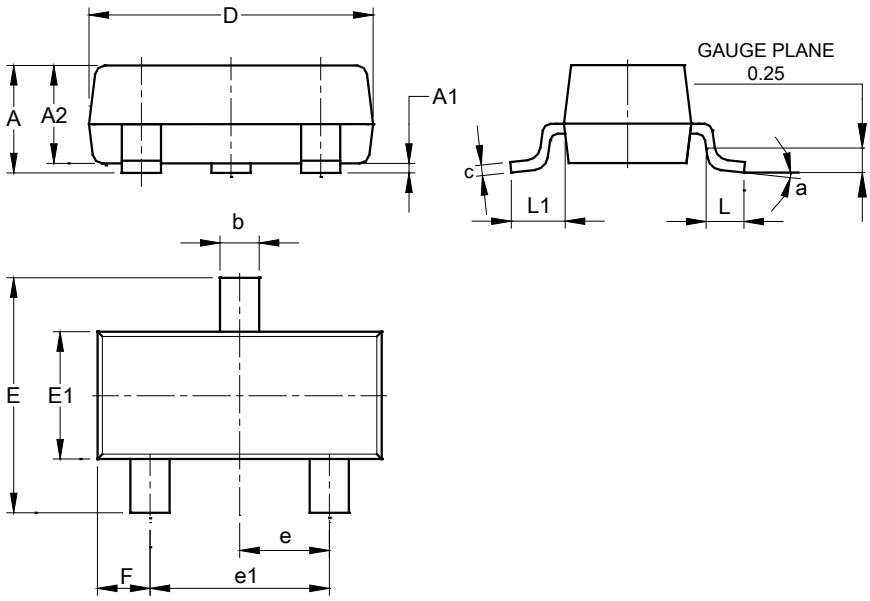


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)

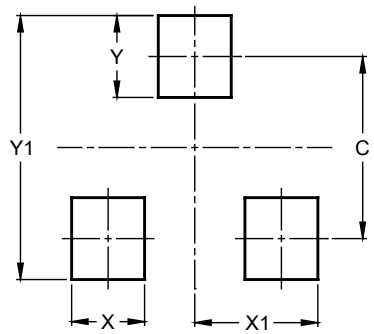


SOT23 (Standard)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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